Ordering number : ENN7020

P-Channel Silicon MOSFET

FTD1014



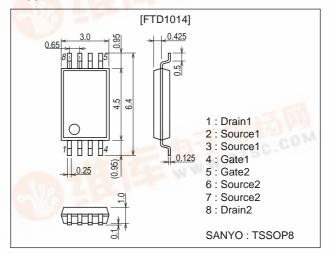
Load Switching Applications

Features

- · Low ON-resistance.
- 2.5V drive.
- Mounting height 1.1mm.
- Composite type, facilitating high-density mounting.

Package Dimensions

unit : mm 2155A



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		-20	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		-2	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-15	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (1000mm ² X0.8mm) 1unit	0.8	W
Total Dissipation	PT	Mounted on a ceramic board (1000mm ² X0.8mm)	1.0	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg	Salus Civis	-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0	-20			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-20V, V _{GS} =0			-1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0	19		±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =-10V, I _D =-1mA	-0.4		-1.4	V
Forward Transfer Admittance	yfs	Vps=-10V, lp=-2A	4.2	6		S

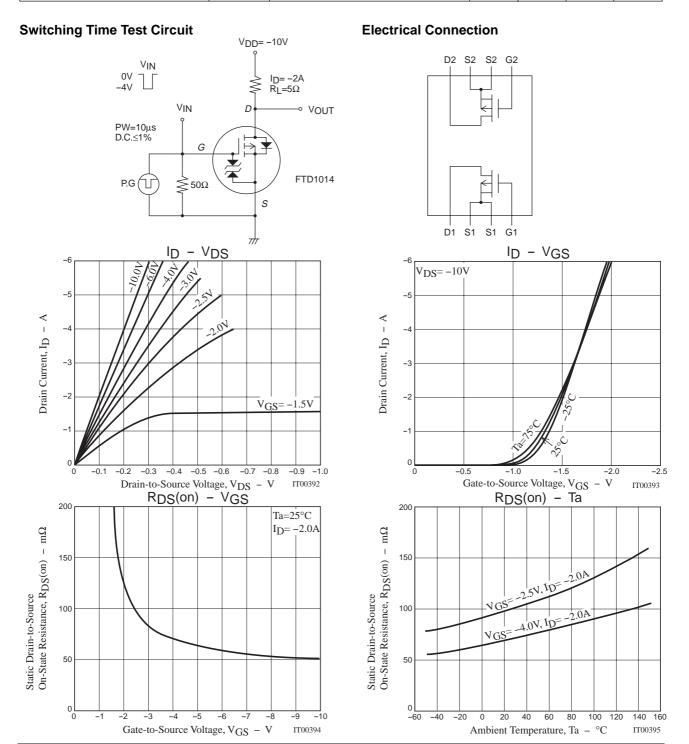
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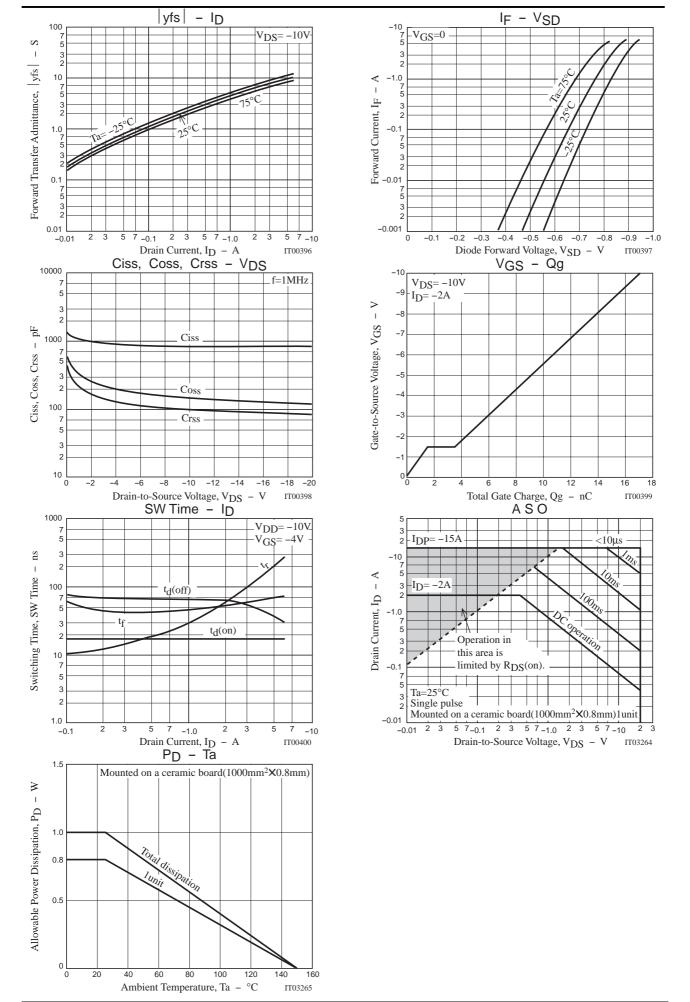
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Parameter	Symbol	Conditions	Ratings			Linit
			min	typ	max	Unit
Static Drain-to-Source On-State Resistance	RDS(on) 1	ID=-2A, VGS=-4V		68	89	$m\Omega$
	R _{DS} (on) 2	I _D =-2A, V _G S=-2.5V		92	130	mΩ
Input Capacitance	Ciss	V _{DS} =-10V, f=1MHz		820		pF
Output Capacitance	Coss	V _{DS} =-10V, f=1MHz		150		pF
Reverse Transfer Capacitance	Crss	V _{DS} =-10V, f=1MHz		100		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit		17		ns
Rise Time	tr	See specified Test Circuit		60		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		66		ns
Fall Time	tf	See specified Test Circuit		56		ns
Total Gate Charge	Qg	V _D S=-10V, V _G S=-10V, I _D =-2A		17		nC
Gate-to-Source Charge	Qgs	V _{DS} =-10V, V _{GS} =-10V, I _D =-2A		1.5		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =-10V, V _{GS} =-10V, I _D =-2A		2		nC
Diode Forward Voltage	VSD	IS=-2A, VGS=0		-0.8	-1.5	V



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